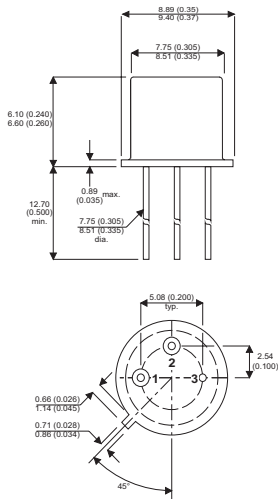


MECHANICAL DATA

Dimensions in mm (inches)



**N-CHANNEL ENHANCEMENT
MODE TRANSISTOR**

FEATURES

- $V_{(BR)DSS} = 200V$
- $I_D = 5.5A$
- $R_{DS(ON)} = 0.40\Omega$

TO-39 METAL PACKAGE

Underside View

PIN 1 – Source PIN 2 – Gate PIN 3 – Drain

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^\circ C$ unless otherwise stated)

V_{DS}	Drain–Source Voltage	200V
V_{GS}	Gate–Source Voltage	$\pm 20V$
I_D	Drain Current Continuous $T_C = 25^\circ C$ $T_C = 100^\circ C$	5.5A 3.5A
I_{DM}	Drain Current Pulsed	22A
I_A	Avalanche Current	3.1A
P_D	Total Device Dissipation @ $T_C = 25^\circ C$ $T_C = 100^\circ C$	25W 10W
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to $+150^\circ C$
THERMAL CHARACTERISTICS		
$R_{\theta JC}$	Thermal Resistance Junction to Case	$5.0^\circ C/W$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	$175^\circ C/W$
T_L	Maximum Lead Temperature 1.5mm from Case for 10 secs.	$300^\circ C$

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain–Source Breakdown Voltage $V_{GS} = 0$ $I_D = 1000\mu\text{A}$	200			V
$V_{GS(th)}$	Gate Threshold Voltage $V_{DS}=V_{GS}$ $I_D = 250\mu\text{A}$	2.0		4.0	
I_{GSS}	Gate–Body Leakage $V_{DS} = 0$ $V_{GS} = \pm 20\text{V}$			100	nA
$I_{D(on)}$	On-State Drain Current ¹ $V_{DS} = 2.2$ $V_{GS} = 10\text{V}$	5.5			A
I_{DSS}	Zero Gate Voltage Drain Current $V_{DS} = 0.8 \times V_{(BR)DSS}$ $V_{GS} = 0$ $T_J = 125^\circ\text{C}$			25	μA
				250	
$r_{DS(on)}$	Drain–Source On–Resistance ¹ $V_{GS} = 10\text{V}$ $I_D = 3.5\text{A}$		0.25	4.0	Ω
g_{fS}	Forward Transconductance ¹ $V_{DS} = 5\text{V}$ $I_D = 3.5\text{A}$	2.5	3.0		$\text{s}(\overline{\circ})$
C_{iss}	Input Capacitance Output capacitance Reverse Transfer Capacitance $V_{DS} = 25\text{V}$ $V_{GS} = 0$ $f = 1.0\text{MHz}$		600		pF
C_{oss}			250		
C_{rSS}			80		
t_{don}	Turn–On Delay Time RiseTime Turn off Delay Time FallTime $V_{DD} = 77\text{V}$ $R_L = 22\Omega$ $I_D = 3.5\text{A}$ $V_{GEN} = 10\text{V}$ $R_G = 7.5 \text{ ohms}$		8	30	ns
t_r			42	50	
$t_{d(of)}$			12	50	
t_f			30	40	
SOURCE DRAIN DIODE RATING CHARACTERISTICS					
V_{SD}	Diode Forward Voltage ¹ $I_F = I_S$ $V_{GS} = 0$			1.4	V
I_S	Continues Current Pulsed Current ²			5.5	A
I_{SM}				22	
t_{rr}	Reverse Recovery Time $I_F = I_S$		150	500	ns
Q_{rr}	Reverse Recovered Charge $di_F/dT = 100\text{A}/\mu\text{S}$			6	μC

- 1) Pulse test : Pulse Width < 300 μs ,Duty Cycle < 2%
- 2) Pulse width limited by maximum junction temperature